Supporting Information

Pyridine-based Electron Transporting Materials for Highly Efficient Organic Solar Cells

Hao-Wu Lin ^{a,*}, Chih-Wei Lu^a, Li-Yen Lin^b, Yi-Hong Chen^a, Wei-Chieh Lin^a, Ken-Tsung Wong^b, Francis Lin^b

1. Effect of electron transporting layer thickness

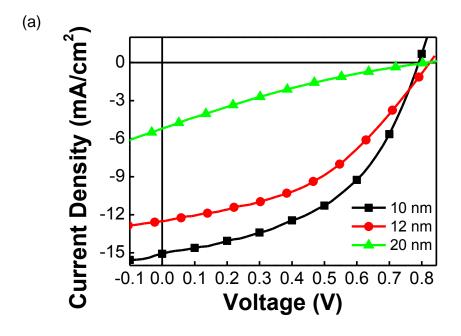
Fig. S1 shows the spectral mismatch corrected *J*-V characteristics of different BCP and TmPyPB thicknesses in the optimized device structure and the device performances are listed in Table S1.

Table S1 Performance parameters of the devices.

Device type	ETL (thickness)	$J_{\rm sc}~({\rm mA/cm^2})$	$V_{oc}(V)$	FF	PCE (%)
	BCP (10 nm)	14.91 ± 0.17	0.78 ± 0.01	0.47 ± 0.01	5.6 ± 0.1
	BCP (12 nm)	12.35 ± 0.16	0.81 ± 0.01	0.42 ± 0.01	4.3 ± 0.1
DTDCTB:C ₇₀	BCP (20 nm)	5.15 ± 0.05	0.81 ± 0.01	0.18 ± 0.01	0.81 ± 0.01
(1:1.6)	TmPyPB (10 nm)	14.61 ± 0.36	0.79 ± 0.01	0.52 ± 0.01	6.1 ± 0.2
	TmPyPB (12 nm)	12.56 ± 0.32	0.81 ± 0.01	0.52 ± 0.01	5.4 ± 0.1
	TmPyPB (20 nm)	1.31 ± 0.20	0.79 ± 0.01	0.21 ± 0.01	0.23 ± 0.04

^a Department of Materials Science and Engineering, National Tsing Hua University, No. 101, Section 2, Kuang-Fu Road, Hsinchu, Taiwan 30013. E-mail: hwlin@mx.nthu.edu.tw

^b Department of Chemistry, National Taiwan University, No.1, Section 4, Roosevelt Road, Taipei, Taiwan 10617.



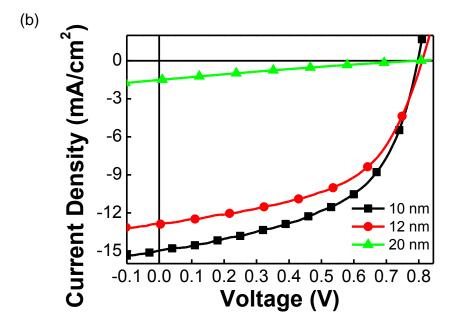


Fig. S1 (a) Mismatch corrected *J*-V characteristics (under 1 sun, AM 1.5G illumination) of the devices with the following structures: ITO/MoO3 (5 nm)/DTDCTB (7 nm)/DTDCTB:C70 (1:1.6 by volume, 40 nm)/C70 (7 nm)/BCP (10, 12, 20 nm)/Ag (150 nm). (b) Mismatch corrected *J*-V characteristics (under 1 sun, AM 1.5G illumination) of the devices with the following structures: ITO/MoO3 (5 nm)/DTDCTB (7 nm)/DTDCTB:C70 (1:1.6 by volume, 40 nm)/C70 (7 nm)/TmPyPB (10, 12, 20 nm)/Ag (150 nm).